

**AMENDMENTS TO THE CLAIMS**

Claims 1-26 (Canceled).

27. (Currently amended) An ~~intermediate structure for an~~ array of resistance variable memory cells comprising:

at least one pillar of stacked material layers on a semiconductor substrate, the stacked layers comprising a first electrode layer, a chalcogenide glass layer material having metal ions diffused therein in contact with the first electrode and being capable of changing resistance under the influence of an applied voltage, a metal material in contact with the chalcogenide glass material, and a second electrode layer in contact with the metal material, the at least one pillar not located within a via.

Claims 28-48 (Canceled).

49. (Previously presented) The array of Claim 27, wherein the metal ions comprise silver ions.

50. (Previously presented) The array of Claim 27, wherein at least one of the first and second electrodes is tungsten.

51. (New) The array of Claim 27, wherein the metal material comprises silver.